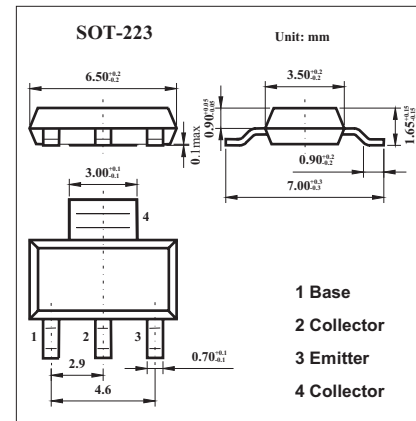


High Voltage Transistor

PZTA96S

■ Features

- PNP Silicon

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Emmitter Voltage	V_{CEO}	-450	V
Collector-Base Voltage	V_{CBO}	-450	V
Emmitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Total Power Dissipation Up to $T_A = 25^\circ\text{C}$ *	P_D	1.5	Watts
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Thermal Resistance from Junction to Ambient *	$R_{\theta JA}$	83.3	$^\circ\text{C}$

* Device mounted on a glass epoxy printed circuit board 1.575 in. X 1.575 in. X 0.059 in.;

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emmitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1.0\text{ mA}, I_B = 0$	-450			V
Collector-Emmitter Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\ \mu\text{A}, I_E = 0$	-450			V
Emmitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\ \mu\text{A}, I_C = 0$	-5.0			V
Collector-Base Cutoff Current	I_{CBO}	$V_{CB} = -400\text{ V}, I_E = 0$			-0.1	μA
Emmitter-Base Cutoff Current	I_{EBO}	$V_{BE} = -4.0\text{ V}, I_C = 0$			-0.1	μA
DC Current Gain*	h_{FE}	$I_C = -10\text{ mA}, V_{CE} = -10\text{ V}$	50		150	
Saturation Voltages	$V_{CE(sat)}$	$I_C = -20\text{ mA}, I_B = -2.0\text{ mA}$			-0.6	V
	$V_{BE(sat)}$	$I_C = -20\text{ mA}, I_B = -2.0\text{ mA}$			-1.0	V

* Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle = 2.0%.

■ Marking

Marking	ZTA96
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